Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Trench MOSFET technology
- Very fast switching
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection

1.3 Applications

- · Charging switch for portable devices
- DC-to-DC converters
- Power management in battery-driven portables
- Hard disk and computing power management

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|------------------------|----------------------------------|--|-----|-----|-----|-----|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | 30 | V |
| V_{GS} | gate-source voltage | | | -12 | - | 12 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | - | 5.5 | Α |
| Static characteristics | | | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 4.5 V; I_{D} = 4.3 A; T_{j} = 25 °C | | - | 37 | 47 | mΩ |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|-----------------------|-----------------|
| 1 | D | drain | 1 6 | D |
| 2 | D | drain | 7 7 | |
| 3 | G | gate | | G T T |
| 4 | S | source | 3 8 4 | \$ 017aaa253 |
| 5 | D | drain | Transparent top view | 07/444250 |
| 6 | D | drain | DFN2020MD-6 (SOT1220) | |
| 7 | D | drain | | |
| 8 | S | source | | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | |
|-------------|-------------|--|---------|--|--|--|
| | Name | Description | Version | | | |
| PMPB33XN | DFN2020MD-6 | plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals | SOT1220 | | | |

4. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PMPB33XN | 1P |

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|--|-----|---------|------------------|-------------------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 30 | V |
| V_{GS} | gate-source voltage | | | -12 | 12 | V |
| I _D | drain current | V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 5.5 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 25 °C | [1] | - | 4.3 | Α |
| | | V _{GS} = 4.5 V; T _{amb} = 100 °C | [1] | - | 2.7 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$ | | - | 17 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [1] | - | 1.5 | W |
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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|----------------------|-----------------------------------|-----|-----|-----|------|
| | | T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 2.4 | W |
| | | T _{sp} = 25 °C | | - | 8.3 | W |
| T _j | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-dra | in diode | | | | | _ |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 1.7 | Α |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

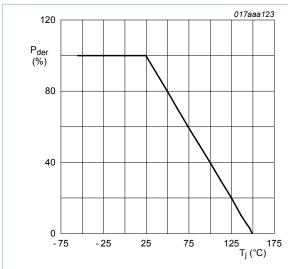


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

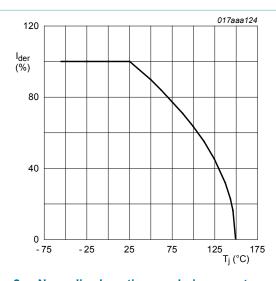


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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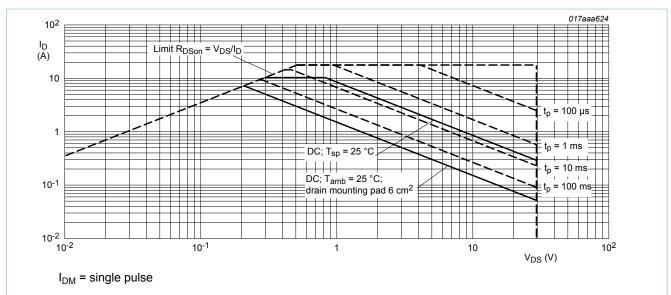


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|-------------|-----|-----|-----|-----|------|
| R _{th(j-a)} thermal resistance from junction to ambient | | in free air | [1] | - | 245 | 280 | K/W |
| | | [2] | - | 74 | 85 | K/W | |
| | ambient | | [3] | - | 45 | 52 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 10 | 15 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm², $t \le 5$ s

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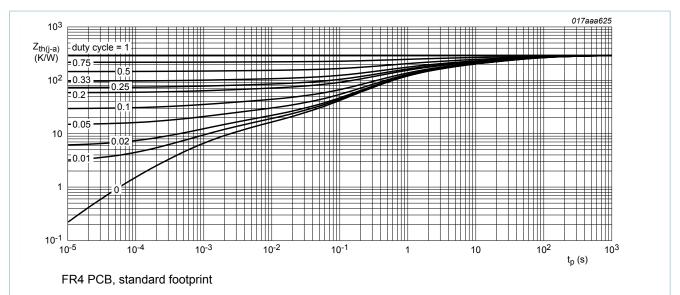


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

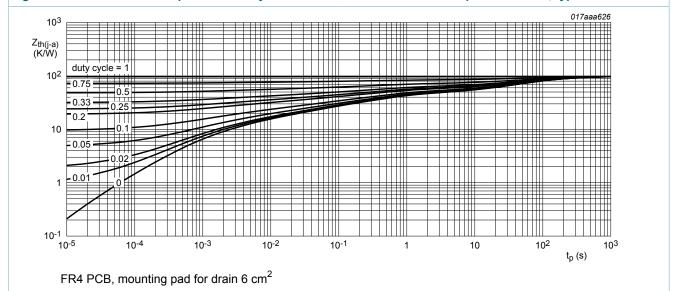


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|-----------------------------------|---|------|---------|-----------------|-----------------|
| Static chara | acteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C | 30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$ | 0.45 | 0.8 | 1.2 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 1 | μA |
| | | V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C | - | - | 100 | μA |
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|------------------------------|--|-----|-----|-----|------|
| I _{GSS} | gate leakage current | V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| | | V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = 4.5 V; I_{D} = 4.3 A; T_{j} = 25 °C | - | 37 | 47 | mΩ |
| | resistance | V_{GS} = 4.5 V; I_D = 4.3 A; T_j = 150 °C | - | 63 | 80 | mΩ |
| | | V_{GS} = 2.5 V; I_{D} = 1 A; T_{j} = 25 °C | - | 55 | 76 | mΩ |
| g _{fs} | forward transconductance | V_{DS} = 10 V; I_{D} = 4.3 A; T_{j} = 25 °C | - | 20 | - | S |
| R_G | gate resistance | f = 1 MHz | - | 9.8 | - | Ω |
| Dynamic cl | haracteristics | | | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = 15 V; I_{D} = 4.3 A; V_{GS} = 4.5 V; T_{j} = 25 °C | - | 5.1 | 7.6 | nC |
| Q _{GS} | gate-source charge | | - | 1 | - | nC |
| Q_{GD} | gate-drain charge | | - | 1.3 | - | nC |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 505 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 57 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 48 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 15 V; I_{D} = 4.3 A; V_{GS} = 4.5 V; | - | 6 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$ | - | 17 | - | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 21 | - | ns |
| t _f | fall time | | - | 20 | - | ns |
| Source-dra | nin diode | | ' | | | |
| V _{SD} | source-drain voltage | $I_S = 1.7 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | 0.8 | 1.2 | V |
| | | · | | | | |

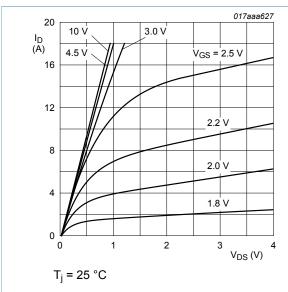


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

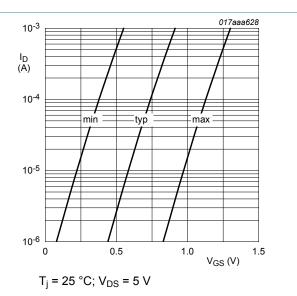


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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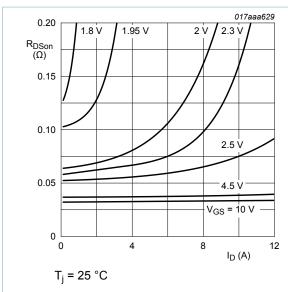


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

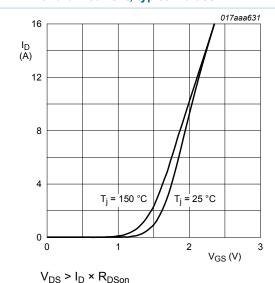


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

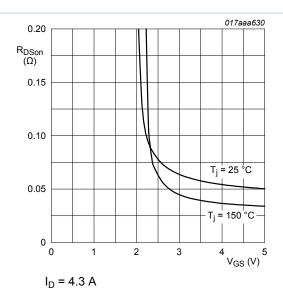


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

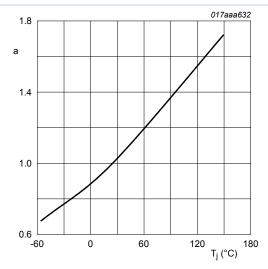


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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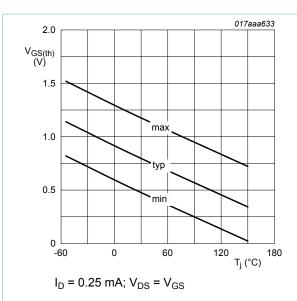


Fig. 12. Gate-source threshold voltage as a function of junction temperature

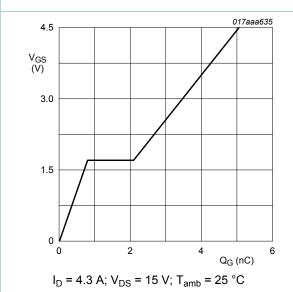


Fig. 14. Gate-source voltage as a function of gate charge; typical values

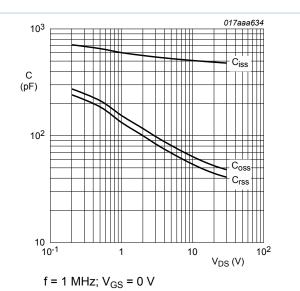


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

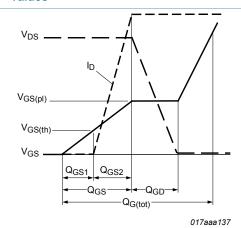
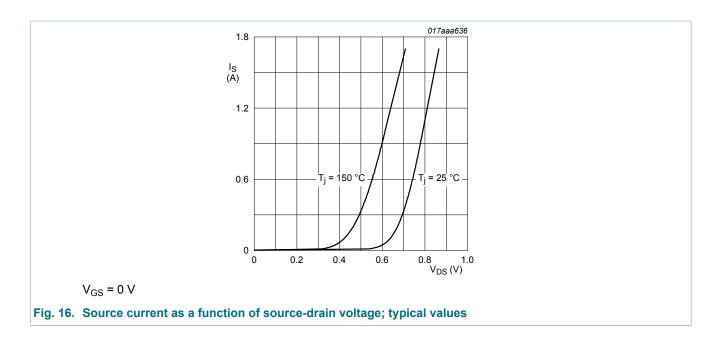
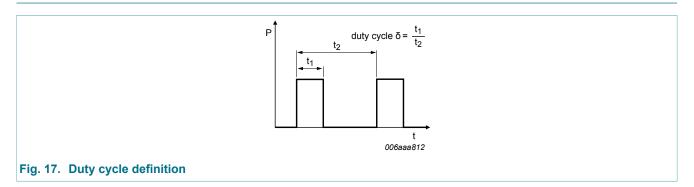


Fig. 15. Gate charge waveform definitions

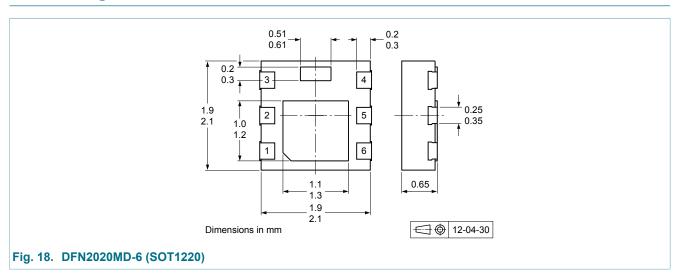
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8. Test information



9. Package outline

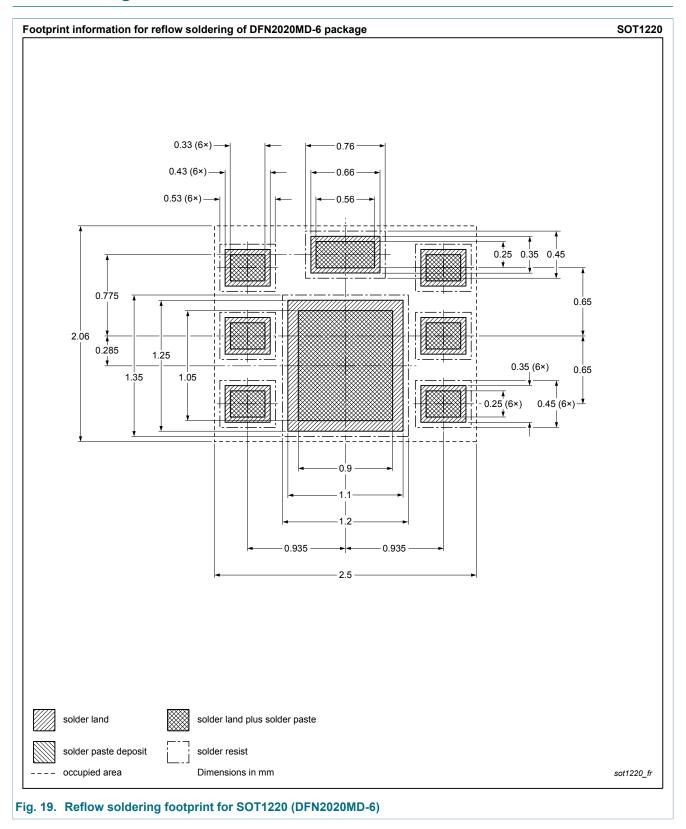


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10. Soldering



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11. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PMPB33XN v.1 | 20120706 | Product data sheet | - | - |

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12. Legal information

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
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